CMD8447

40V N-Channel MOSFET

General Description

This N-Channel MOSFET has been produced using advanced trench technology to deliver low RDS(on) and optimized BVDSS capability to offer superior performance benefit in the application

Product Summary

BVDSS	RDSON	ID
40V	9mΩ	50A

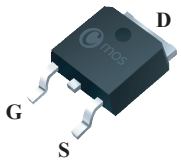
Applications

- Inverters
- Power Supplies

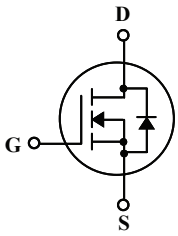
Features

- Max $r_{DS(on)}$ = 9mΩ at V_{GS} = 10V
- Max $r_{DS(on)}$ = 11mΩ at V_{GS} = 4.5V
- Fast Switching
- RoHS Compliant

TO-252 Pin Configuration



TO-252
(CMD8447)



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	50	A
I_{DM}	Pulsed Drain Current	150	A
E_{AS}	Drain-Source Avalanche Energy [1]	61.5	mJ
P_D@T_C=25℃	Total Power Dissipation	45	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	40	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	2.8	℃/W

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance [2]	V_{GS}=10V , I_D=20A	---	---	9	mΩ
		V_{GS}=4.5V , I_D=15A	---	---	11	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250 uA	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=32V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS} =±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance [2]	V_{DS}=10 V, I_D=9A	---	13	---	S
Q_g	Total Gate Charge	I_D=14A V_{DS} =20V V_{GS} =10V	---	37	---	nC
Q_{gs}	Gate-Source Charge		---	6	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS} =20V I_D=1A R_{GEN} =6Ω V_{GS} =10 V	---	12	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	38	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	2100	---	pF
C_{oss}	Output Capacitance		---	200	---	
C_{rss}	Reverse Transfer Capacitance		---	120	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse Recovery Time	I_F=14A di/dt=100A/μs	---	22	---	ns
Q_{rr}	Reverse Recovery Charge		---	11	---	nC
V_{SD}	Diode Forward Voltage [2]	V_{GS}=0V , I_S=14 A	---	---	1.2	V

Notes:

1.Starting T_J = 25℃, L= 0.1mH, I_{AS} = 35A, V_{DD} = 15 V, V_{GS} = 10 V .

2.Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.